



**THIS SPEC IS OBSOLETE**

Spec No: 001-55636

Spec Title: CY62148VN MOBL (R), 4 MBIT (512K X 8) STATIC RAM

Sunset Owner: Ramesh Raghavan (RAME)

Replaced by: None

## Features

- Wide Voltage Range: 2.7V to 3.6V
- Ultra Low Active Power
- Low Standby Power
- TTL-compatible Inputs and Outputs
- Automatic Power Down when deselected
- CMOS for optimum Speed and Power
- Package available in a 32-Pin TSOP II and a 32-Pin SOIC Package

## Functional Description

The CY62148VN is a high performance CMOS static RAM organized as 512K words by eight bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable

applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption by 99 percent when addresses are not toggling. The device can be put into standby mode when deselected (CE HIGH).

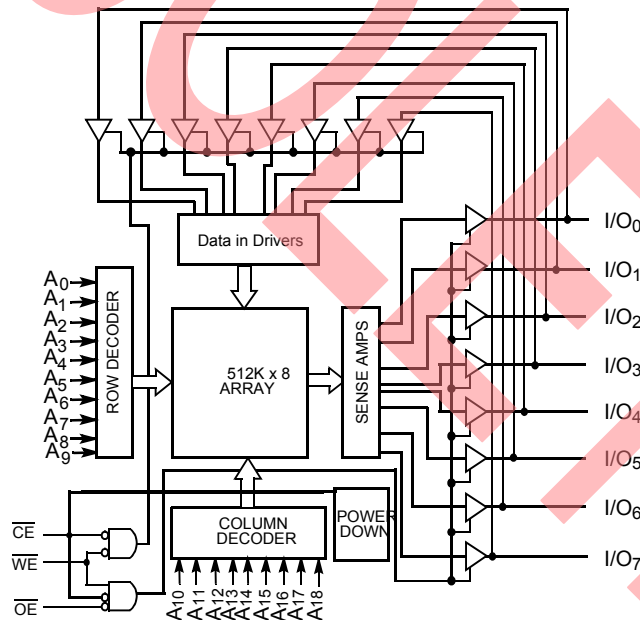
Writing to the device is accomplished by taking Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. Data on the eight I/O pins ( $I/O_0$  through  $I/O_7$ ) is then written into the location specified on the address pins ( $A_0$  through  $A_{18}$ ).

Reading from the device is accomplished by taking Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing Write Enable ( $\overline{WE}$ ) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the I/O pins.

The eight input/output pins ( $I/O_0$  through  $I/O_7$ ) are placed in a high impedance state when the device is deselected ( $\overline{CE}$  HIGH), the outputs are disabled ( $\overline{OE}$  HIGH), or during a write operation ( $\overline{CE}$  LOW and  $\overline{WE}$  LOW).

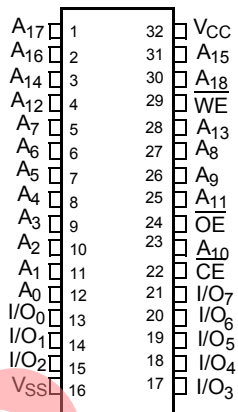
For best practice recommendations, refer to the Cypress application note [AN1064, SRAM System Guidelines](#).

## Logic Block Diagram



## Pin Configuration

Figure 1. 32-Pin TSOP II/SOIC (Top View)



## Product Portfolio

Product	V <sub>CC</sub> Range (V)			Speed (ns)	Power Dissipation			
					Operating I <sub>CC</sub> , (mA)		Standby I <sub>SB2</sub> , (μA)	
	Min	Typ <sup>[1]</sup>	Max		Typ <sup>[1]</sup>	Max	Typ <sup>[1]</sup>	Max
CY62148VNLL	2.7	3.0	3.6	70	7	15	2	20

### Note

1. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ.)</sub>, T<sub>A</sub> = 25°C.

## Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. User guidelines are not tested.

Storage Temperature ..... -65°C to +150°C

Ambient Temperature with  
Power Applied ..... 55°C to +125°C

Supply Voltage to Ground Potential ..... -0.5V to +4.6V

DC Voltage Applied to Outputs  
in High-Z State<sup>[2]</sup> ..... -0.5V to  $V_{CC} + 0.5V$

DC Input Voltage<sup>[2]</sup> ..... -0.5V to  $V_{CC} + 0.5V$

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... > 2001V  
(per MIL-STD-883, Method 3015)

Latch up Current ..... > 200 mA

## Operating Range

Range	Ambient Temperature	$V_{CC}$
Industrial	-40°C to +85°C	2.7V to 3.6V

## Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions	CY62148VN-70			Unit
			Min.	Typ. <sup>[1]</sup>	Max.	
$V_{OH}$	Output HIGH Voltage	$I_{OH} = -1.0 \text{ mA}$ $V_{CC} = 2.7V$	2.4			V
$V_{OL}$	Output LOW Voltage	$I_{OL} = 2.1 \text{ mA}$ $V_{CC} = 2.7V$			0.4	V
$V_{IH}$	Input HIGH Voltage	$V_{CC} = 3.6V$	2.2		$V_{CC} + 0.5V$	V
$V_{IL}$	Input LOW Voltage	$V_{CC} = 2.7V$	-0.5		0.8	V
$I_{IX}$	Input Load Current	$GND \leq V_I \leq V_{CC}$	-1	+1	+1	μA
$I_{OZ}$	Output Leakage Current	$GND \leq V_O \leq V_{CC}$ , Output Disabled	-1	+1	+1	μA
$I_{CC}$	$V_{CC}$ Operating Supply Current	$I_{OUT} = 0 \text{ mA}$ , $f = f_{MAX} = 1/t_{RC}$ CMOS Levels $V_{CC} = 3.6V$		7	15	mA
		$I_{OUT} = 0 \text{ mA}$ , $f = 1 \text{ MHz}$ CMOS Levels		1	2	
$I_{SB1}$	Automatic CE Power down Current—CMOS Inputs	$CE \geq V_{CC} - 0.3V$ , $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$ , $f = f_{MAX}$		2	20	μA
$I_{SB2}$	Automatic CE Power down Current—CMOS Inputs	$CE \geq V_{CC} - 0.3V$ $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$ , $f = 0$ $V_{CC} = 3.6V$				

## Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Max	Unit
$C_{IN}$	Input Capacitance	$T_A = 25^\circ\text{C}$ , $f = 1 \text{ MHz}$ , $V_{CC} = 3.0V$	6	pF
$C_{OUT}$	Output Capacitance		8	pF

## Thermal Resistance

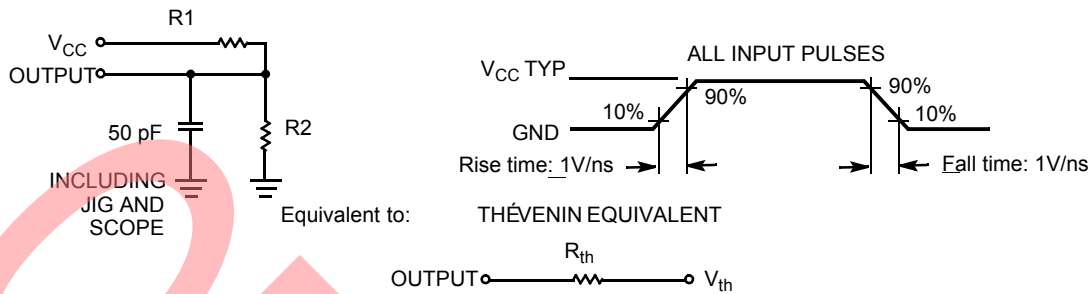
Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	TSOP II	SOIC	Unit
$\Theta_{JA}$	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 4.25 x 1.125 inch, four-layer printed circuit board	TBD	TBD	°C/W
$\Theta_{JC}$	Thermal Resistance (Junction to Case)		TBD	TBD	°C/W

### Note

2.  $V_{IL(min.)} = -2.0V$  for pulse durations less than 20 ns.

**Figure 2. AC Test Loads and Waveforms**



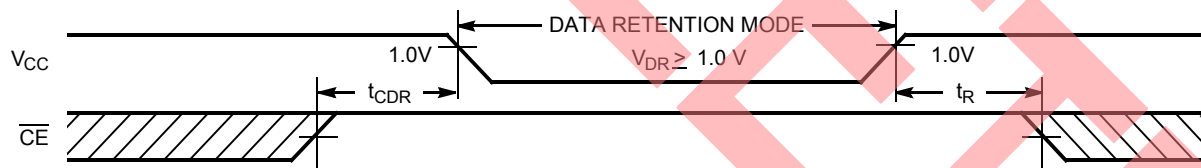
Parameters	3.0V	Unit
R1	1105	$\Omega$
R2	1550	$\Omega$
R <sub>TH</sub>	645	$\Omega$
V <sub>TH</sub>	1.75V	V

### Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min.	Typ. <sup>[1]</sup>	Max.	Unit
V <sub>DR</sub>	V <sub>CC</sub> for Data Retention		1.0		3.6	V
I <sub>CCDR</sub>	Data Retention Current	V <sub>CC</sub> = 1.0V, CE ≥ V <sub>CC</sub> - 0.3V, V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.3V or V <sub>IN</sub> ≤ 0.3V; No input may exceed V <sub>CC</sub> + 0.3V		0.2	5.5	μA
t <sub>CDR</sub> <sup>[3]</sup>	Chip Deselect to Data Retention Time		0			ns
t <sub>R</sub> <sup>[4]</sup>	Operation Recovery Time		t <sub>RC</sub>			ns

**Figure 3. Data Retention Waveform**



### Notes

3. Tested initially and after any design or process changes that may affect these parameters.
4. Full-device AC operation requires linear V<sub>CC</sub> ramp from V<sub>DR</sub> to V<sub>CC(min.)</sub> ≥ 10 μs or stable at V<sub>CC(min.)</sub> ≥ 10 μs.

## Switching Characteristics

Over the Operating Range<sup>[5]</sup>

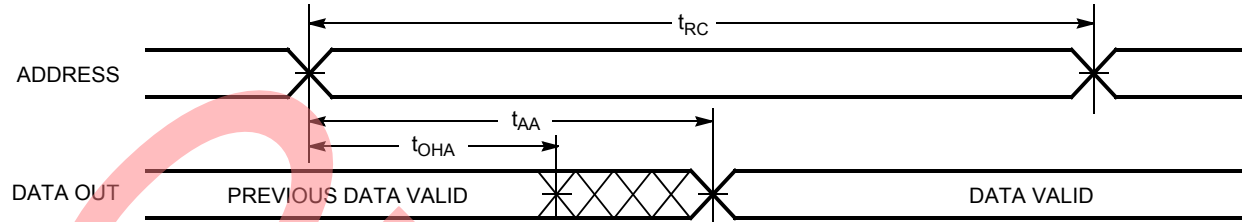
Parameter	Description	70 ns		Unit
		Min	Max	
Read Cycle				
t <sub>RC</sub>	Read Cycle Time	70		ns
t <sub>AA</sub>	Address to Data Valid		70	ns
t <sub>OHA</sub>	Data Hold from Address Change	10		ns
t <sub>ACE</sub>	$\overline{CE}$ LOW to Data Valid		70	ns
t <sub>DOE</sub>	$\overline{OE}$ LOW to Data Valid		35	ns
t <sub>LZOE</sub>	$\overline{OE}$ LOW to Low Z <sup>[6]</sup>	5		ns
t <sub>HZOE</sub>	$\overline{OE}$ HIGH to High Z <sup>[7]</sup>		25	ns
t <sub>LZCE</sub>	$\overline{CE}$ LOW and to Low Z <sup>[6]</sup>	10		ns
t <sub>HZCE</sub>	$\overline{CE}$ HIGH to High Z <sup>[6, 7]</sup>		25	ns
t <sub>PU</sub>	$\overline{CE}_1$ LOW and CE <sub>2</sub> HIGH to Power Up	0		ns
t <sub>PD</sub>	$\overline{CE}_1$ HIGH and CE <sub>2</sub> LOW to Power Down		70	ns
Write Cycle <sup>[8, 9]</sup>				
t <sub>WC</sub>	Write Cycle Time	70		ns
t <sub>SCE</sub>	$\overline{CE}_1$ LOW and CE <sub>2</sub> HIGH to Write End	60		ns
t <sub>AW</sub>	Address Setup to Write End	60		ns
t <sub>HA</sub>	Address Hold from Write End	0		ns
t <sub>SA</sub>	Address Setup to Write Start	0		ns
t <sub>PWE</sub>	$\overline{WE}$ Pulse Width	50		ns
t <sub>SD</sub>	Data Setup to Write End	30		ns
t <sub>HD</sub>	Data Hold from Write End	0		ns
t <sub>HZWE</sub>	$\overline{WE}$ LOW to High Z <sup>[6, 7]</sup>		25	ns
t <sub>LZWE</sub>	$\overline{WE}$ HIGH to Low Z <sup>[6]</sup>	10		ns

### Notes

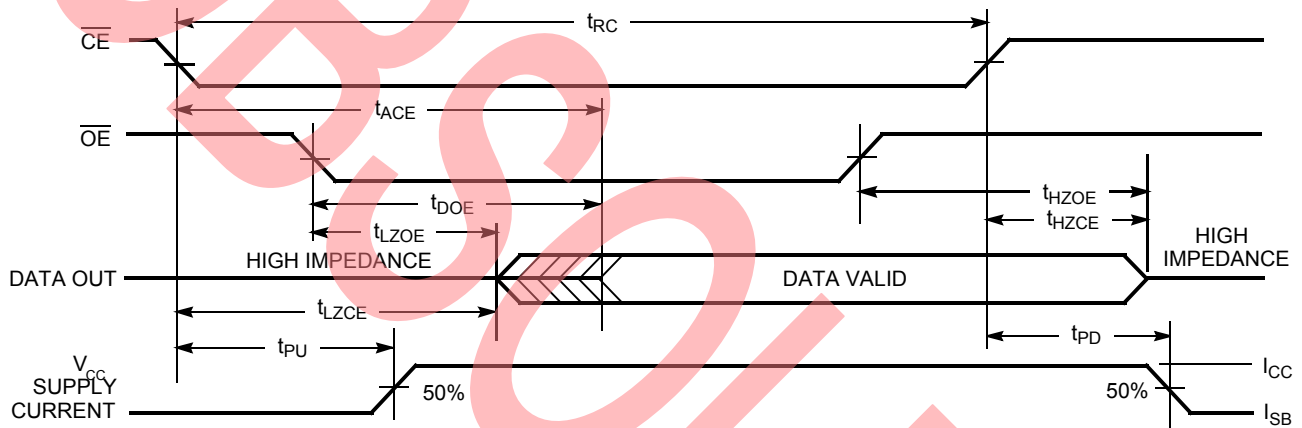
- Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to  $V_{CC(typ.)}$ , and output loading of the specified  $I_{OL}/I_{OH}$  and 30 pF load capacitance.
- At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any given device.
- $t_{HZOE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  are specified with  $C_L = 5$  pF as in (b) of AC Test Loads. Transition is measured  $\pm 200$  mV from steady-state voltage.
- The internal write time of the memory is defined by the overlap of  $\overline{CE}$  LOW and  $\overline{WE}$  LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
- The minimum write cycle time for Write Cycle #3 ( $\overline{WE}$  controlled,  $\overline{OE}$  LOW) is the sum of  $t_{HZWE}$  and  $t_{SD}$ .

## Switching Waveforms

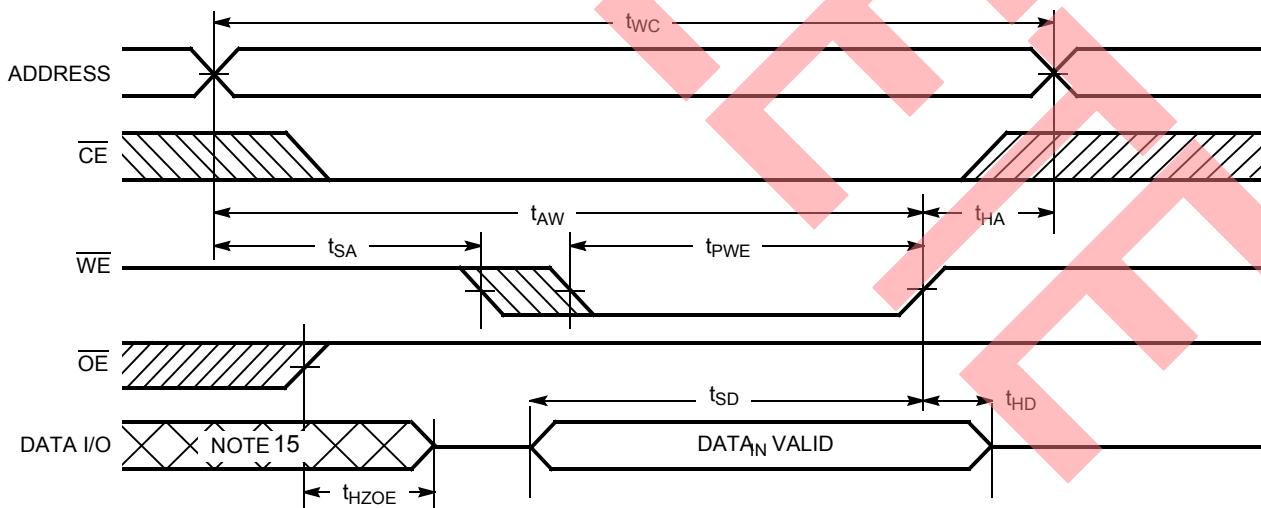
**Figure 4. Read Cycle No. 1: Address Transition Controlled** [10, 11]



**Figure 5. Read Cycle No. 2:  $\overline{OE}$  Controlled** [11, 12]



**Figure 6. Write Cycle No 1:  $\overline{WE}$  Controlled** [8, 13, 14]

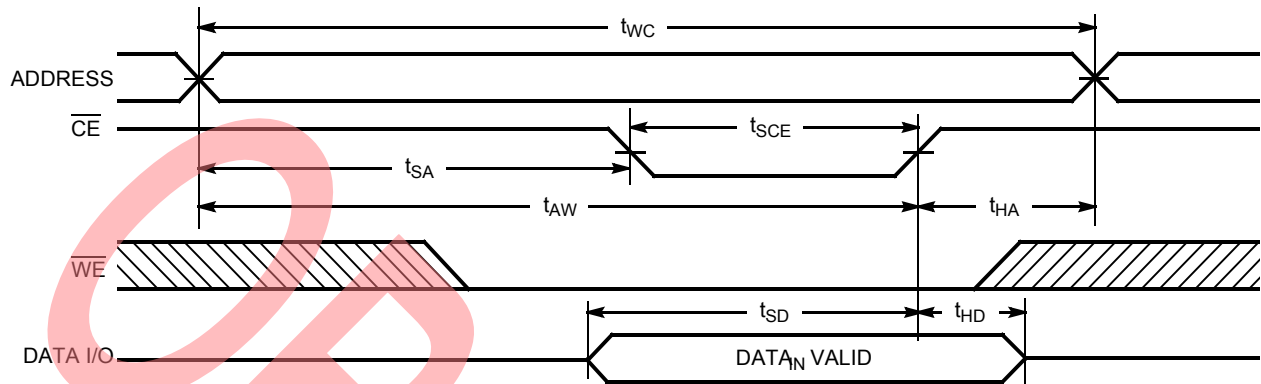


### Notes

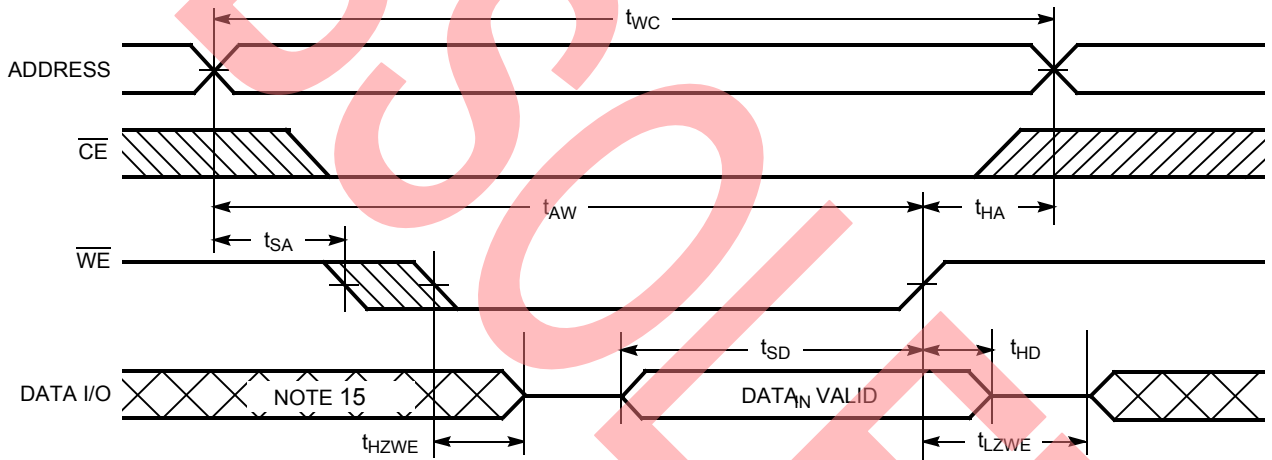
10. The device is continuously selected.  $\overline{OE}$ ,  $\overline{CE}$  =  $V_{IL}$ .
11.  $\overline{WE}$  is HIGH for read cycle.
12. Address valid before or similar to  $\overline{CE}$  transition LOW.
13. Data I/O is high impedance if  $\overline{OE}$  =  $V_{IH}$ .
14. If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  =  $V_{IH}$ , the output remains in a high impedance state.

## Switching Waveforms (continued)

**Figure 7. Write Cycle 2:  $\overline{\text{CE}}$  Controlled [8, 13, 14]**



**Figure 8. Write Cycle 3:  $\overline{\text{WE}}$  controlled,  $\overline{\text{OE}}$  LOW [14]**

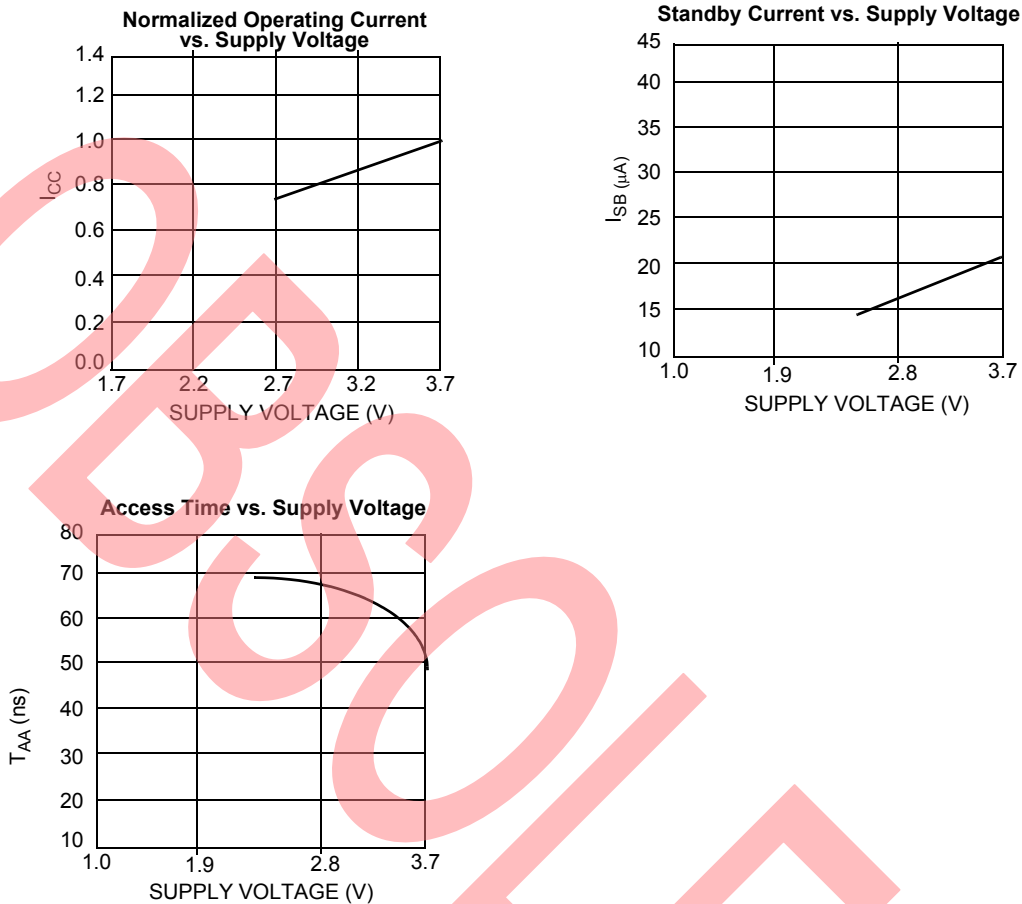


### Note

15. During this period, the I/Os are in output state. Do not apply input signals.



## Typical DC and AC Characteristics



## Truth Table

CE	WE	OE	Inputs/Outputs	Mode	Power
H	X	X	High-Z	Deselect/Power down	Standby ( $I_{SB}$ )
L	H	L	Data Out	Read	Active ( $I_{CC}$ )
L	L	X	Data In	Write	Active ( $I_{CC}$ )
L	H	H	High-Z	Output Disabled	Active ( $I_{CC}$ )

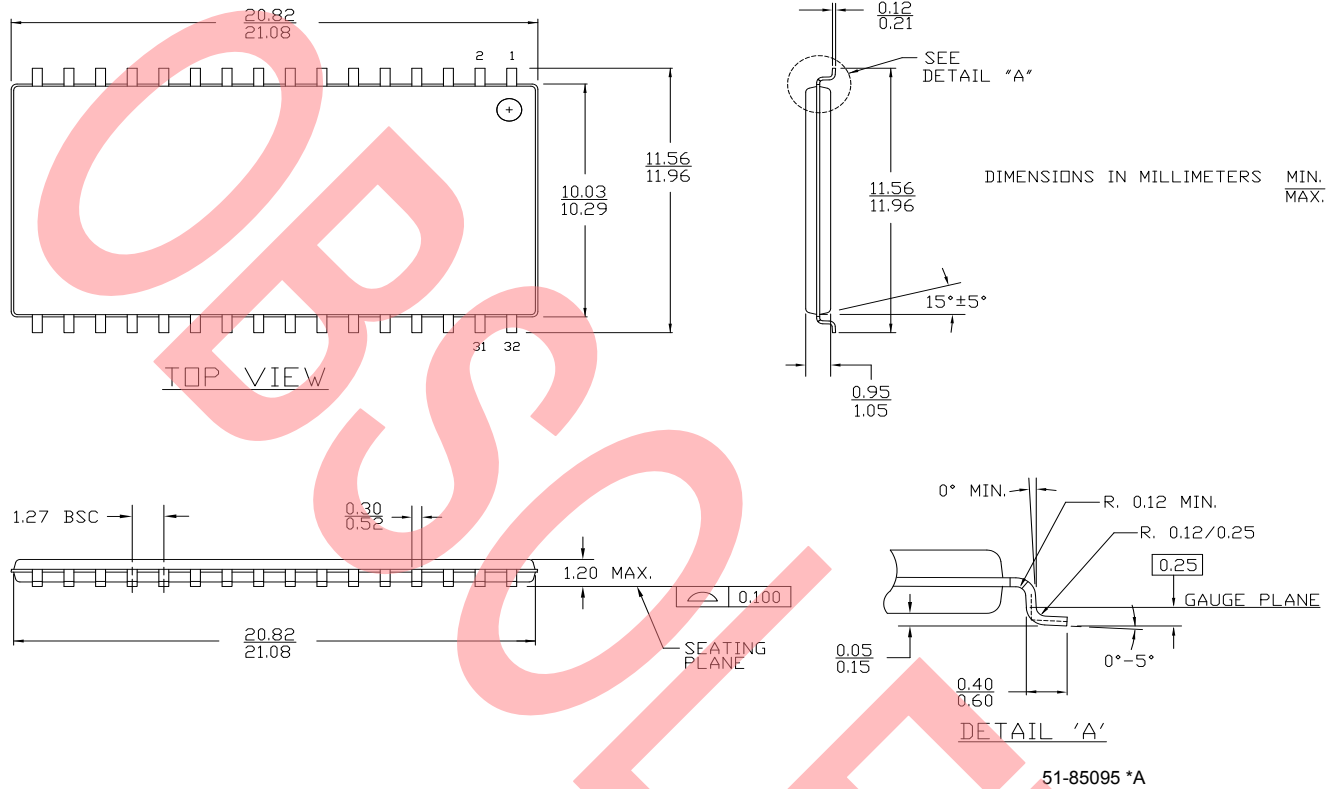
## Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
70	CY62148VNLL-70ZSX1	51-85095	32-Pin TSOP II	Industrial

## Package Diagrams

Figure 9. 32-Pin TSOP II, 51-85095

### 32 Lead TSOP TYPE II



## Document History Page

Document Title: CY62148VN MoBL®, 4 Mbit (512K x 8) Static RAM Document Number: 001-55636				
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
**	2761558	VKN	09/09/2009	New data sheet
*A	2905443	VKN	06/04/2010	Removed inactive part CY62148VNLL-70SXI from ordering information. Updated Package Diagrams.
*B	3111176	RAME	12/15/2010	Obsolete Datasheet. The part specified in the ordering information is not active part number.

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